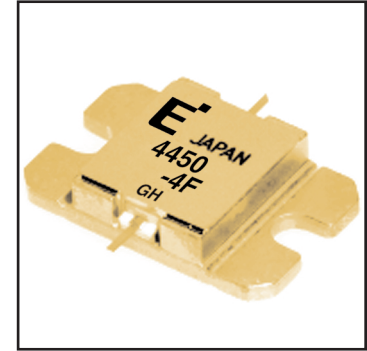


FEATURES

- High Output Power: $P_{1dB} = 36.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 11.0\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 37\%$ (Typ.)
- Low $IM_3 = -46\text{dBc}$ @ $P_o = 25.5\text{dBm}$
- Broad Band: 4.4 ~ 5.0GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



DESCRIPTION

The FLM4450-4F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25^\circ\text{C}$	25.0	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -2.2 mA respectively with gate resistance of 100 Ω .

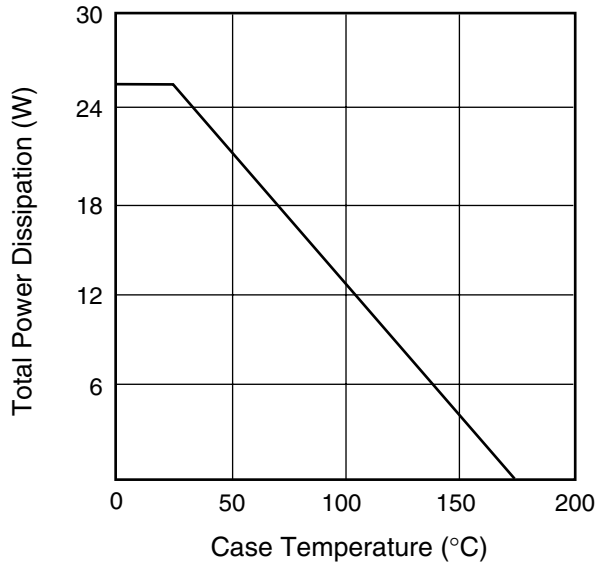
ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	1950	2900	mA
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 1100\text{mA}$	-	1000	-	mS
Pinch-off Voltage	V_p	$V_{DS} = 5\text{V}, I_{DS} = 90\text{mA}$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -90\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.55 I_{DSS}$ (Typ.), $f = 4.4 \sim 5.0 \text{GHz},$ $Z_S = Z_L = 50 \text{ohm}$	35.5	36.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		10.0	11.0	-	dB
Drain Current	I_{dsr}		-	1100	1300	mA
Power-added Efficiency	η_{add}		-	37	-	%
Gain Flatness	ΔG		-	-	± 0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 5.0 \text{GHz}, \Delta f = 10 \text{MHz}$ 2-Tone Test $P_{out} = 25.5\text{dBm}$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	5.0	6.0	$^\circ\text{C}/\text{W}$
Channel Temperature Rise	ΔT_{ch}	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$

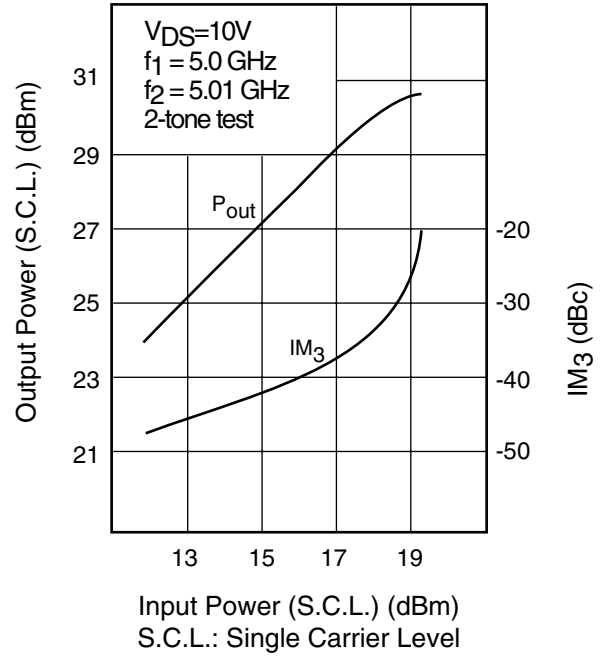
CASE STYLE: IB

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

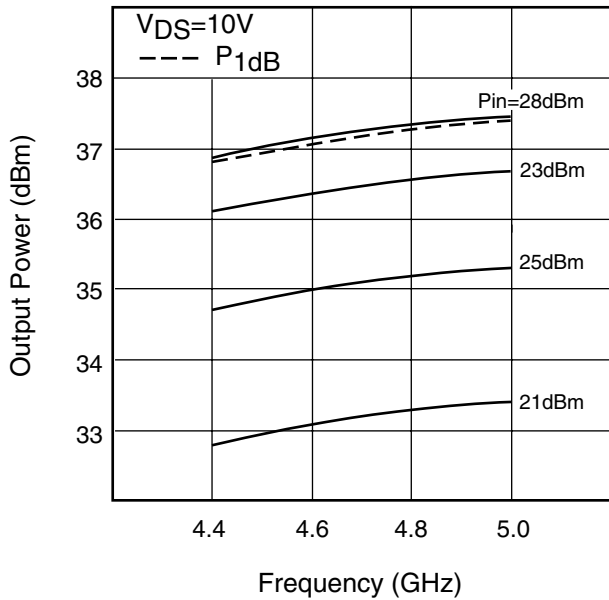
POWER DERATING CURVE



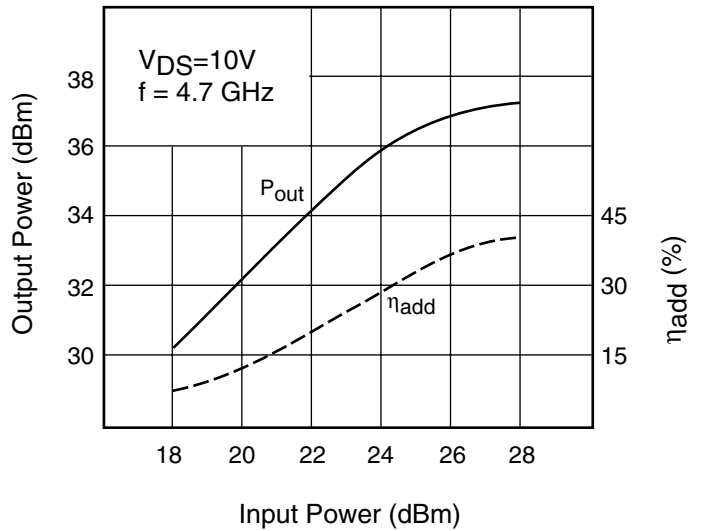
OUTPUT POWER & IM₃ vs. INPUT POWER



OUTPUT POWER vs. FREQUENCY

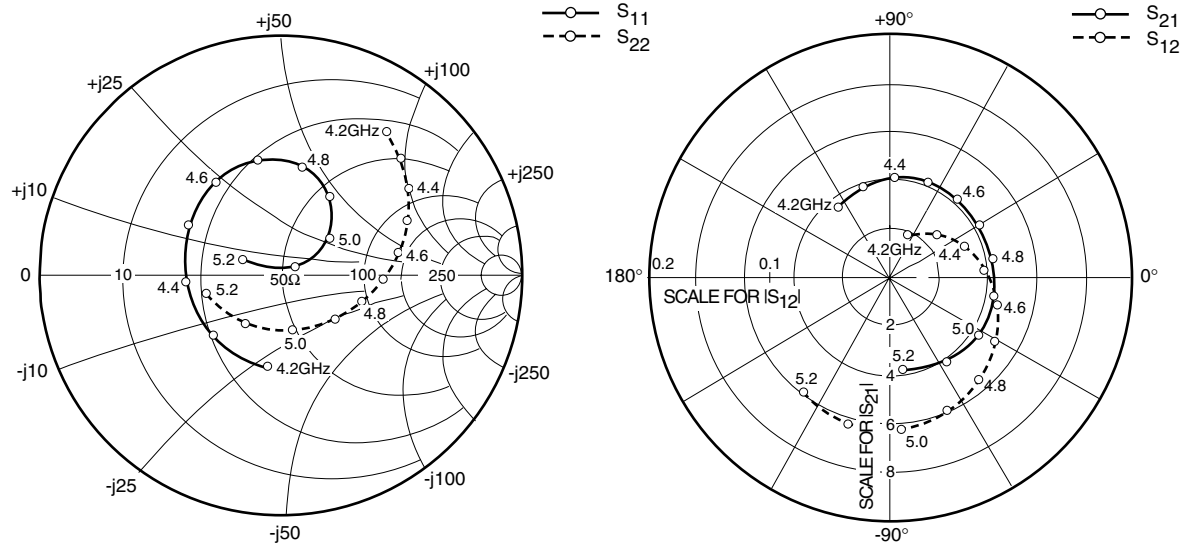


OUTPUT POWER vs. INPUT POWER



FLM4450-4F

C-Band Internally Matched FET



S-PARAMETERS

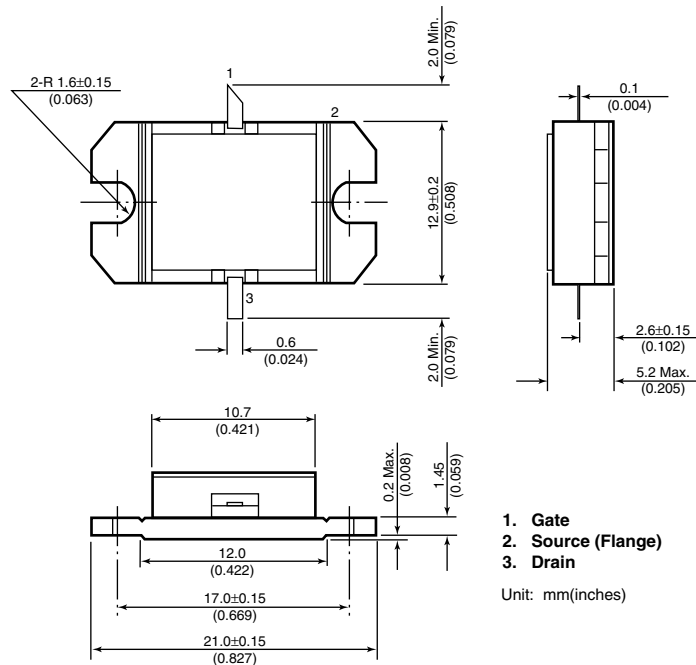
$V_{DS} = 10V, I_{DS} = 1100mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
4200	.388	-98.6	3.672	126.7	.039	62.7	.740	53.8
4300	.373	-139.1	3.921	107.5	.052	42.8	.700	44.0
4400	.397	-176.6	4.081	87.9	.066	22.9	.640	34.1
4500	.443	151.5	4.166	68.3	.078	3.8	.565	23.3
4600	.471	124.2	4.220	49.0	.090	-14.3	.487	11.3
4700	.487	100.8	4.250	29.8	.100	-31.6	.422	-2.2
4800	.455	78.6	4.290	10.1	.111	-49.2	.354	-18.7
4900	.385	57.7	4.318	-10.7	.118	-66.9	.284	-41.1
5000	.256	36.6	4.308	-32.9	.125	-85.9	.236	-77.7
5100	.066	29.7	4.173	-57.2	.125	-106.4	.253	-124.7
5200	.170	156.7	3.828	-82.7	.118	-128.0	.317	-165.0

FLM4450-4F

C-Band Internally Matched FET

Case Style "IB" Metal-Ceramic Hermetic Package



For further information please contact:

Eudyna Devices USA Inc.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
TEL: (408) 232-9500
FAX: (408) 428-9111
www.us.eudyna.com

Eudyna Devices Europe Ltd.

Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
United Kingdom
TEL: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

Eudyna Devices Asia Pte Ltd.

Hong Kong Branch
Rm. 1101, Ocean Centre, 5 Canton Rd.
Tsim Sha Tsui, Kowloon, Hong Kong
TEL: +852-2377-0227
FAX: +852-2377-3921

Eudyna Devices Inc.

Sales Division
1, Kanai-cho, Sakae-ku
Yokohama, 244-0845, Japan
TEL: +81-45-853-8156
FAX: +81-45-853-8170

CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

Eudyna Devices Inc. reserves the right to change products and specifications without notice. The information does not convey any license under rights of Eudyna Devices Inc. or others.

© 2004 Eudyna Devices USA Inc.
Printed in U.S.A.

Eudyna